

Philips

Diode BYV27-600

Datasheet

Silicon Diode

BYV27-600

600V/1.6A

DATASHEET

OEM – Philips

Source: Philips Databook 1999

Ultra fast low-loss controlled avalanche rectifiers

BYV27 series

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.

DESCRIPTION

Rugged glass SOD57 package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.



MAM047

Fig.1 Simplified outline (SOD57) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	50	V
	BYV27-50			100	V
	BYV27-100			150	V
	BYV27-150			200	V
	BYV27-200			300	V
	BYV27-300			400	V
	BYV27-400			500	V
	BYV27-500			600	V
V_R	continuous reverse voltage		–	50	V
	BYV27-50			100	V
	BYV27-100			150	V
	BYV27-150			200	V
	BYV27-200			300	V
	BYV27-300			400	V
	BYV27-400			500	V
	BYV27-500			600	V
$I_{F(AV)}$	average forward current	$T_{tp} = 85^\circ\text{C}$; lead length = 10 mm; see Figs 2, 3 and 4; averaged over any 20 ms period; see also Figs 14, 15 and 16	–	2.0	A
	BYV27-50 to 200			1.9	A
	BYV27-300 and 400			1.6	A
	BYV27-500 and 600				
$I_{F(AV)}$	average forward current	$T_{amb} = 60^\circ\text{C}$; printed-circuit board mounting (see Fig. 25); see Figs 5, 6 and 7; averaged over any 20 ms period; see also Figs 14, 15 and 16	–	1.30	A
	BYV27-50 to 200			1.25	A
	BYV27-300 and 400			1.10	A
	BYV27-500 and 600				

**Ultra fast low-loss
controlled avalanche rectifiers**

BYV27 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{FRM}	repetitive peak forward current BYV27-50 to 400 BYV27-500 and 600	$T_{tp} = 85^\circ\text{C}$; see Figs 8, 9 and 10	—	20	A
I_{FRM}	—	—	—	16	A
I_{FRM}	repetitive peak forward current BYV27-50 to 200 BYV27-300 and 400 BYV27-500 and 600	$T_{amb} = 60^\circ\text{C}$; see Figs 11, 12 and 13	—	14	A
I_{FRM}	—	—	—	13	A
I_{FSM}	non-repetitive peak forward current BYV27-50 to 400 BYV27-500 and 600	$t = 10 \text{ ms half sine wave}$; $T_j = T_{j,max}$ prior to surge; $V_R = V_{RRMmax}$	—	50	A
I_{FSM}	—	—	—	40	A
E_{RSM}	non-repetitive peak reverse avalanche energy	$L = 120 \text{ mH}$; $T_j = T_{j,max}$ prior to surge; inductive load switched off	—	20	mJ
T_{stg}	storage temperature		-65	+175	°C
T_j	junction temperature	see Fig. 17	-65	+175	°C

ELECTRICAL CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage BYV27-50 to 200 BYV27-300 and 400 BYV27-500 and 600	$I_F = 2 \text{ A}$; $T_j = T_{j,max}$; see Figs 18, 19 and 20	—	—	0.78	V
V_F	—	—	—	—	0.82	V
V_F	—	—	—	—	1.00	V
V_F	forward voltage BYV27-50 to 200 BYV27-300 and 400 BYV27-500 and 600	$I_F = 2 \text{ A}$; see Figs 18, 19 and 20	—	—	0.98	V
V_F	—	—	—	—	1.05	V
V_F	—	—	—	—	1.25	V
$V_{(BR)R}$	reverse avalanche breakdown voltage BYV27-50 BYV27-100 BYV27-150 BYV27-200 BYV27-300 BYV27-400 BYV27-500 BYV27-600	$I_R = 0.1 \text{ mA}$	55	—	—	V
$V_{(BR)R}$	—	—	110	—	—	V
$V_{(BR)R}$	—	—	165	—	—	V
$V_{(BR)R}$	—	—	220	—	—	V
$V_{(BR)R}$	—	—	330	—	—	V
$V_{(BR)R}$	—	—	440	—	—	V
$V_{(BR)R}$	—	—	560	—	—	V
$V_{(BR)R}$	—	—	675	—	—	V
I_R	reverse current BYV27-50 to 400	$V_R = V_{RRMmax}$; see Fig. 21	—	—	5	μA
I_R	—	$V_R = V_{RRMmax}$; $T_j = 165^\circ\text{C}$; see Fig. 21	—	—	150	μA

**Ultra fast low-loss
controlled avalanche rectifiers**

BYV27 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t_{rr}	reverse recovery time BYV27-50 to 200 BYV27-300 to 600	when switched from $I_F = 0.5 \text{ A}$ to $I_R = 1 \text{ A}$; measured at $I_R = 0.25 \text{ A}$; see Fig. 27	—	—	25	ns
C_d	diode capacitance BYV27-50 to 200 BYV27-300 and 400 BYV27-500 and 600	$f = 1 \text{ MHz}$; $V_R = 0$; see Figs 22, 23 and 24	—	100	—	pF
$\left \frac{dI_R}{dt} \right $	maximum slope of reverse recovery current	when switched from $I_F = 1 \text{ A}$ to $V_R \geq 30 \text{ V}$ and $dI_F/dt = -1 \text{ A}/\mu\text{s}$; see Fig. 26	—	—	4	A/ μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th,j-tp}$	thermal resistance from junction to tie-point	lead length = 10 mm	46	K/W
$R_{th,j-a}$	thermal resistance from junction to ambient	note 1	100	K/W

Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer $\geq 40 \mu\text{m}$, see Fig. 25.
For more information please refer to the 'General Part of Handbook SC01'.

**Ultra fast low-loss
controlled avalanche rectifiers**

BYV27 series

GRAPHICAL DATA

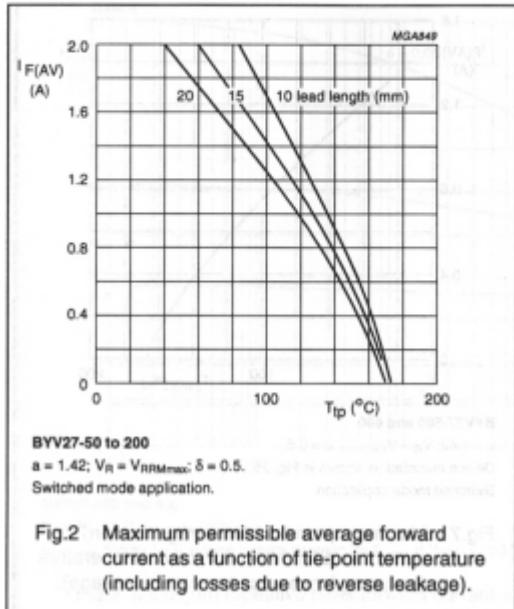


Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

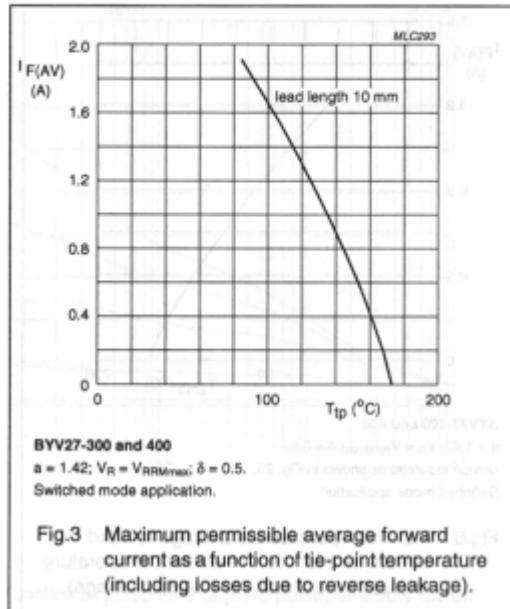


Fig.3 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

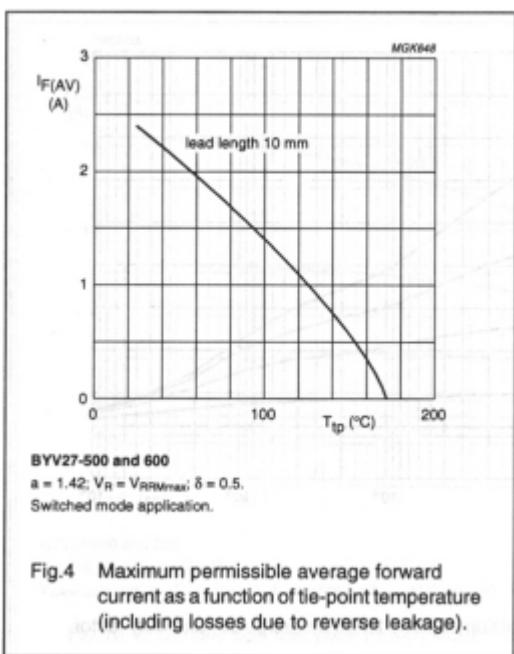


Fig.4 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

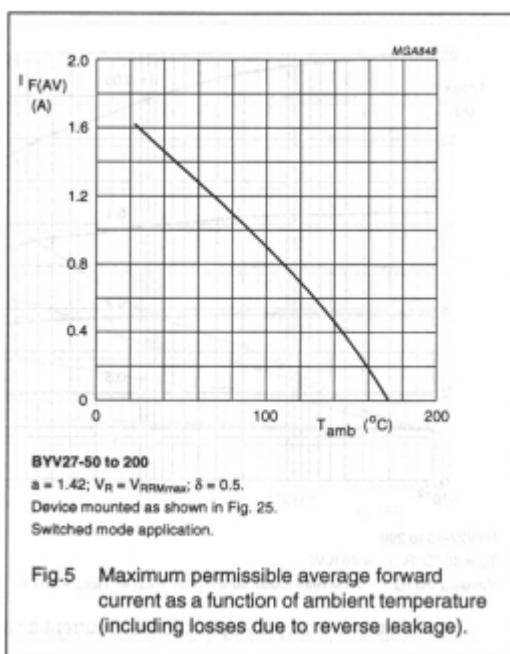
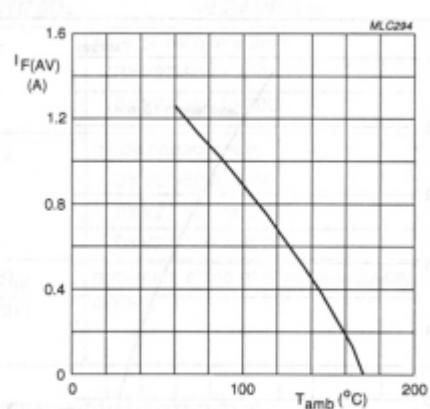


Fig.5 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

**Ultra fast low-loss
controlled avalanche rectifiers**

BYV27 series



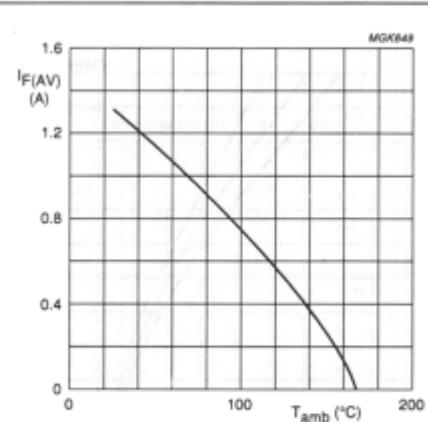
BYV27-300 and 400

$\alpha = 1.42$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

Device mounted as shown in Fig. 25.

Switched mode application.

Fig.6 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).



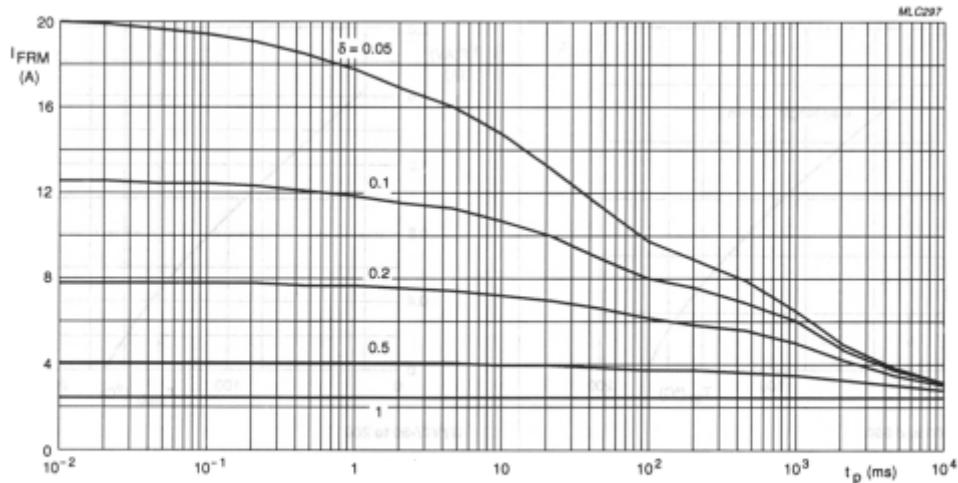
BYV27-500 and 600

$\alpha = 1.42$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

Device mounted as shown in Fig. 25.

Switched mode application.

Fig.7 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).



BYV27-50 to 200

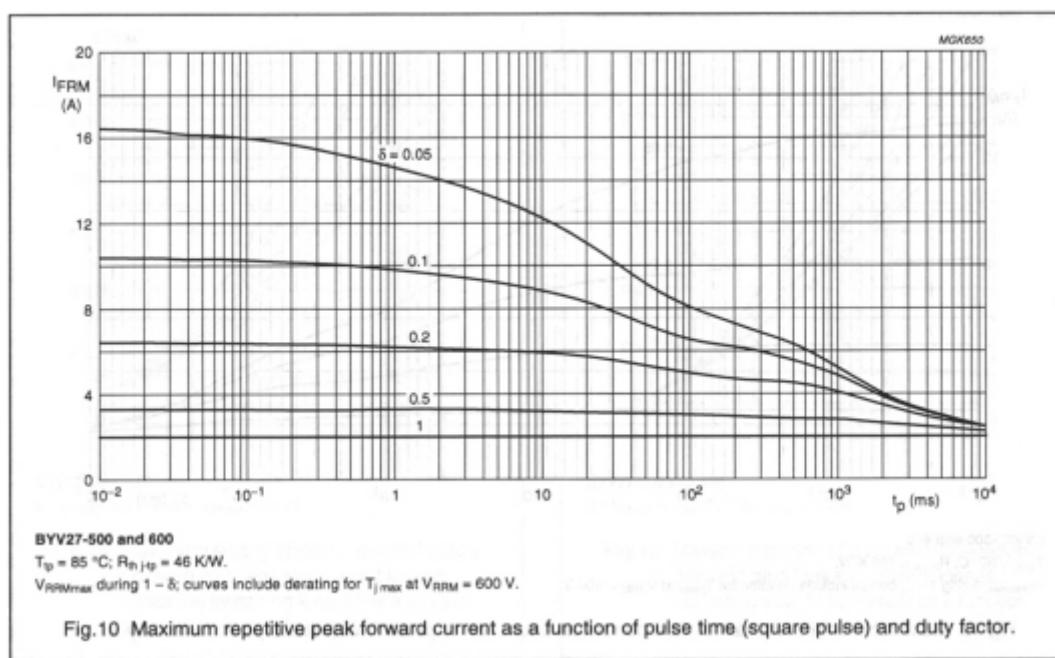
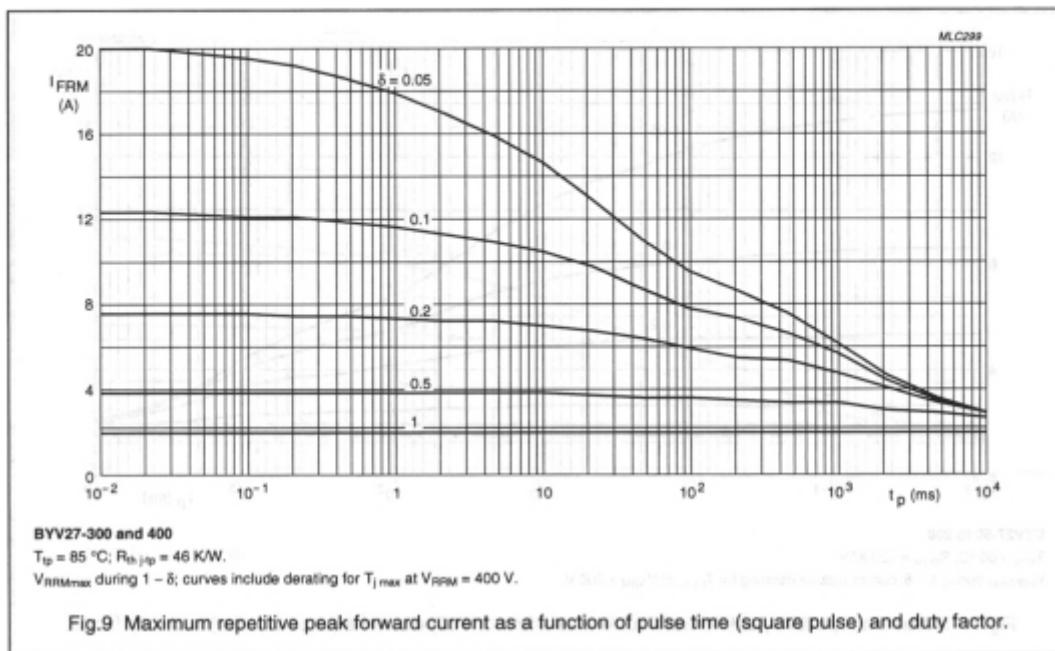
$T_{tp} = 85^\circ\text{C}$; $R_{th,jtp} = 46 \text{ K/W}$.

V_{RRMmax} during 1 – δ ; curves include derating for T_{jmax} at $V_{RRM} = 200 \text{ V}$.

Fig.8 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

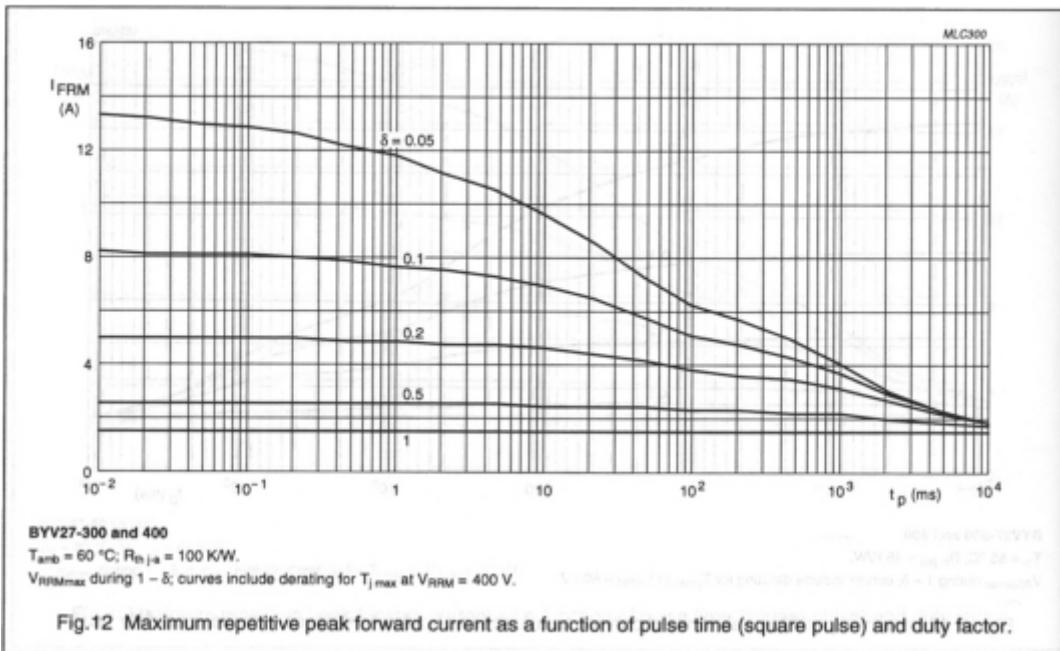
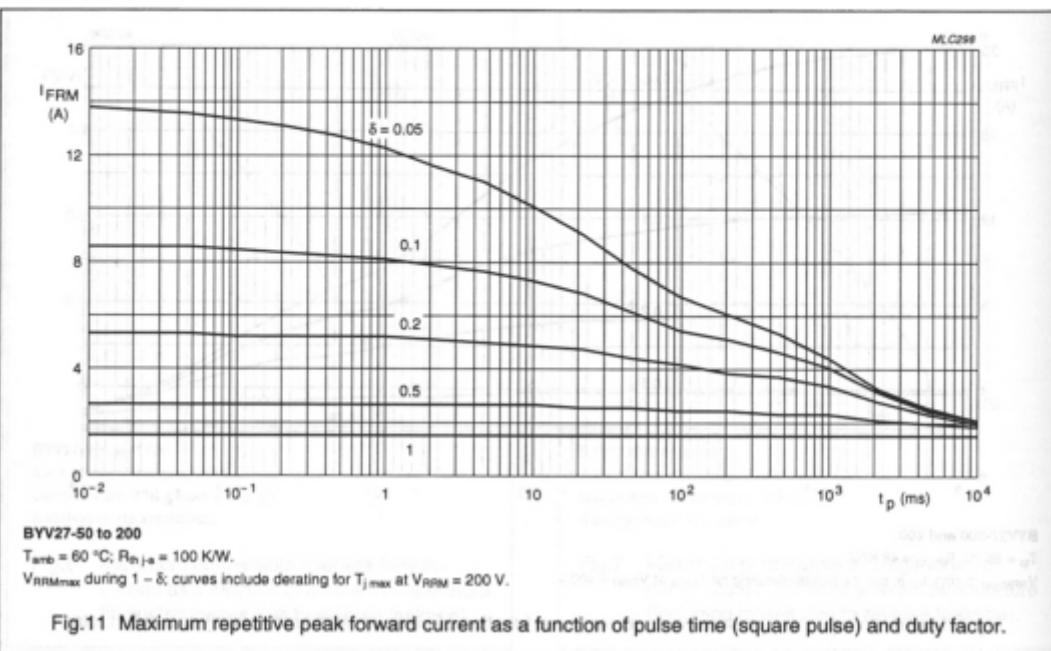
**Ultra fast low-loss
controlled avalanche rectifiers**

BYV27 series



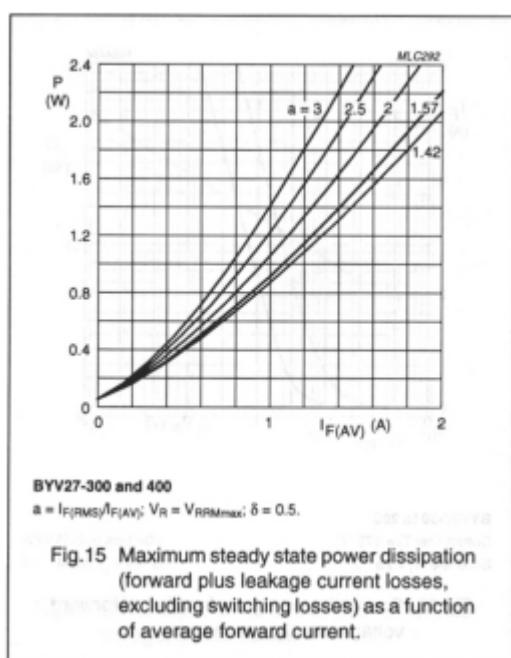
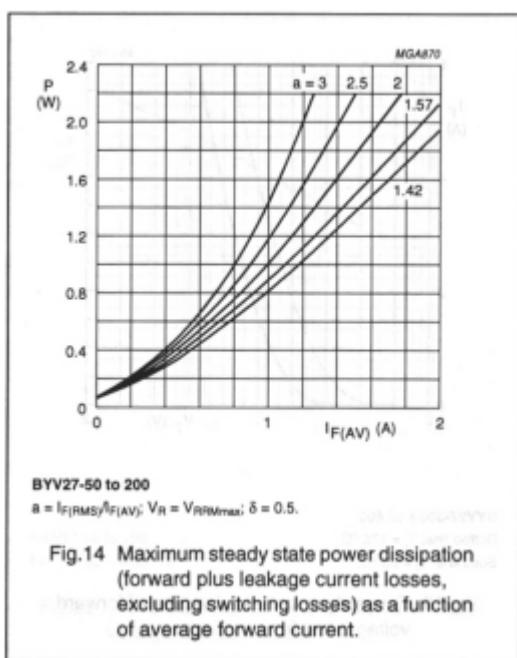
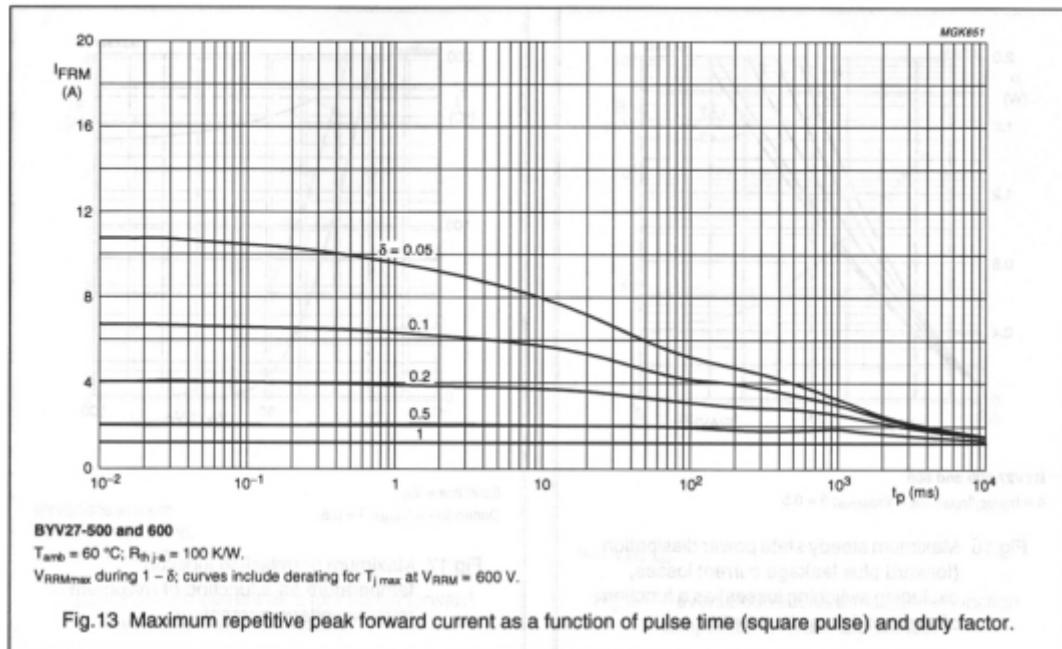
**Ultra fast low-loss
controlled avalanche rectifiers**

BYV27 series



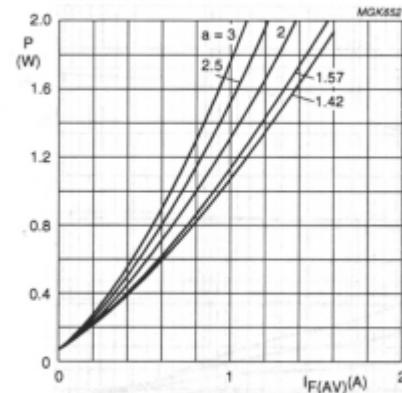
**Ultra fast low-loss
controlled avalanche rectifiers**

BYV27 series



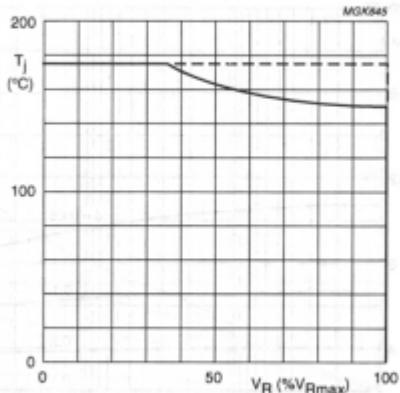
**Ultra fast low-loss
controlled avalanche rectifiers**

BYV27 series



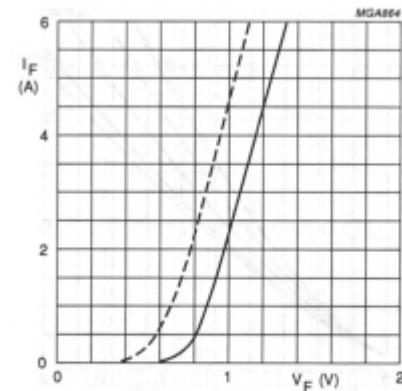
BYV27-500 and 600
 $a = I_F(\text{RMS})/I_F(\text{AV})$; $V_R = V_{\text{RRMmax}}$; $\delta = 0.5$.

Fig.16 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



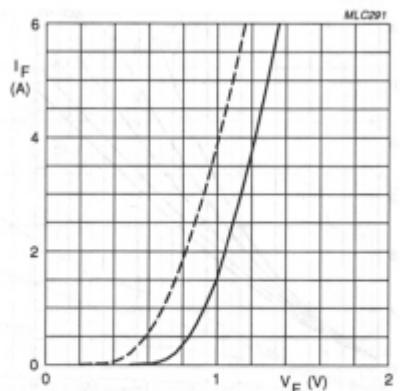
Solid line = V_R .
Dotted line = V_{RRM} ; $\delta = 0.5$.

Fig.17 Maximum permissible junction temperature as a function of maximum reverse voltage percentage.



BYV27-50 to 200
Dotted line: $T_j = 175$ °C.
Solid line: $T_j = 25$ °C.

Fig.18 Forward current as a function of forward voltage; maximum values.

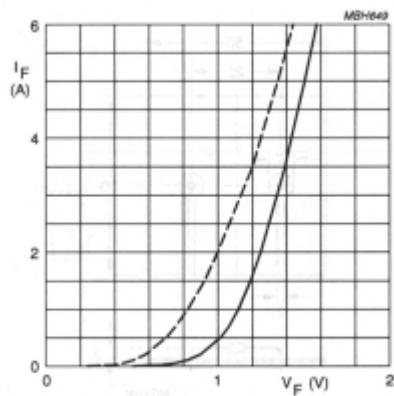


BYV27-300 and 400
Dotted line: $T_j = 175$ °C.
Solid line: $T_j = 25$ °C.

Fig.19 Forward current as a function of forward voltage; maximum values.

**Ultra fast low-loss
controlled avalanche rectifiers**

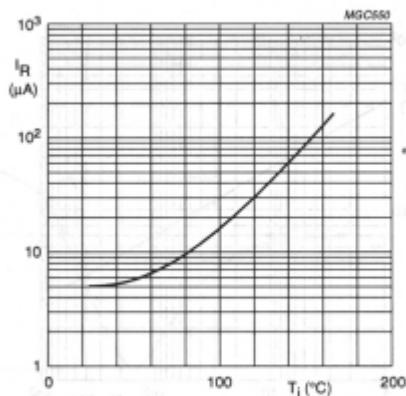
BYV27 series



BYV27-500 and 600

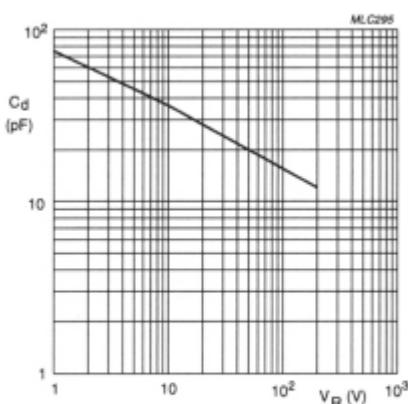
Dotted line: $T_j = 175^\circ C$.
Solid line: $T_j = 25^\circ C$.

Fig.20 Forward current as a function of forward voltage; maximum values.



$V_R = V_{RRMmax}$

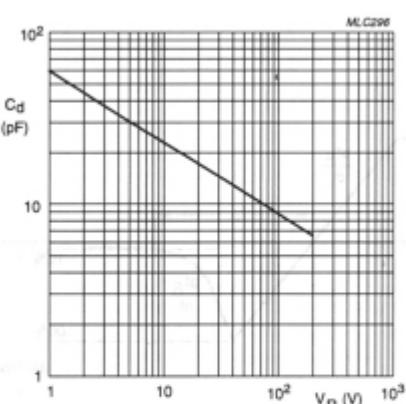
Fig.21 Reverse current as a function of junction temperature; maximum values.



BYV27-50 to 200

f = 1 MHz; $T_j = 25^\circ C$.

Fig.22 Diode capacitance as a function of reverse voltage; typical values.



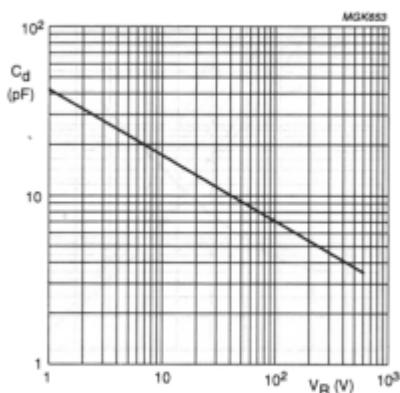
BYV27-300 and 400

f = 1 MHz; $T_j = 25^\circ C$.

Fig.23 Diode capacitance as a function of reverse voltage; typical values.

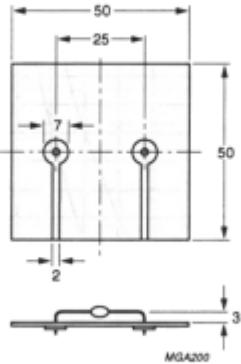
Ultra fast low-loss
controlled avalanche rectifiers

BYV27 series



BYV27-500 and 600
 $f = 1 \text{ MHz}$; $T_j = 25^\circ\text{C}$.

Fig.24 Diode capacitance as a function of reverse voltage; typical values.



Dimensions in mm.

Fig.25 Device mounted on a printed-circuit board.

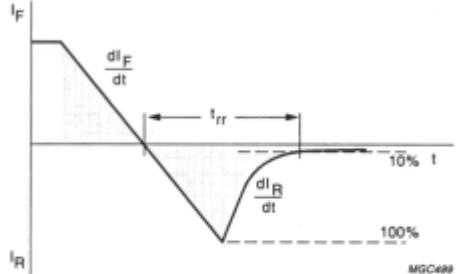
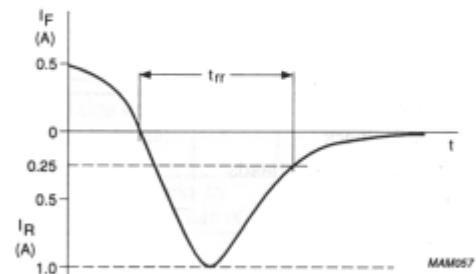
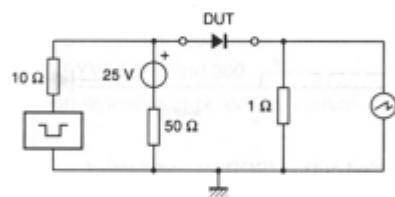


Fig.26 Reverse recovery definitions.

Ultra fast low-loss
controlled avalanche rectifiers

BYV27 series



Input impedance oscilloscope: $1 \text{ M}\Omega$, 22 pF ; $t_r \leq 7 \text{ ns}$.
Source impedance: 50Ω ; $t_r \leq 15 \text{ ns}$.

Fig.27 Test circuit and reverse recovery time waveform and definition.